



PRODUCT DATA SHEET



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Datasheet



Resources

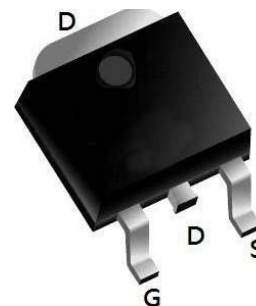


Samples

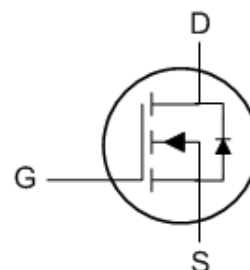
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

Product Summary

BVDSS	RDS(on)	ID
60V	6.8mΩ	65A



TO252 Pin Configuration



- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage (V _{GS} =0V)	60	V
V _{GS}	Gate-Source Voltage (V _{DS} =0V)	±20	V
I _{D (DC)}	Drain Current (DC) at Tc=25°C	65	A
I _{D (DC)}	Drain Current (DC) at Tc=100°C	45	A
I _{DM (pulse)}	Drain Current-Continuous@ Current-Pulsed (Note 1)	260	A
dv/dt	Peak Diode Recovery Voltage	8	V/ns
P _D	Maximum Power Dissipation(Tc=25°C)	75	W
	Derating Factor	0.5	W/°C
E _{AS}	Single Pulse Avalanche Energy (Note 2)	300	mJ
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.EAS condition:T_J=25°C,V_{DD}=33V,V_G=10V

Thermal Characteristic

Symbol	Parameter	Value	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	---	2.0	$^{\circ}C/W$

Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	60	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V _{DS} =64V,V _{GS} =0V	---	---	1	μA
I _{DSS}	Zero Gate Voltage Drain Current(Tc=125℃)	V _{DS} =64V,V _{GS} =0V	---	---	10	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	---	---	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250μA	2	---	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =40A	---	6.8	8.2	mΩ
Dynamic Characteristics						
g _{FS}	Forward Transconductance	V _{DS} =10V,I _D =15A	15	---	---	S
C _{iss}	Input Capacitance	V _{DS} =25V,V _{GS} =0V, f=1.0MHz	---	2873	---	pF
C _{oss}	Output Capacitance		---	252	---	pF
C _{rss}	Reverse Transfer Capacitance		---	205	---	pF
Q _g	Total Gate Charge	V _{DS} =50V,I _D =40A, V _{GS} =10V	---	56	---	nC
Q _{gs}	Gate-Source Charge		---	10	---	nC
Q _{gd}	Gate-Drain Charge		---	16	---	nC
Switching Times						
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V,I _D =2A,R _L =15Ω V _{GS} =10V,R _G =2.5Ω	---	14.5	---	nS
t _r	Turn-on Rise Time		---	24	---	nS
t _{d(off)}	Turn-Off Delay Time		---	45	---	nS
t _f	Turn-Off Fall Time		---	22	---	nS
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current(Body Diode)		---	65	---	A
I _{SDM}	Pulsed Source-Drain Current(Body Diode)		---	260	---	A
V _{SD}	Forward On Voltage ^(Note 1)	T _J =25℃,I _{SD} =40A,V _{GS} =0V	---	0.89	0.99	V
t _{rr}	Reverse Recovery Time ^(Note 1)	T _J =25℃,I _F =75A di/dt=100A/μs	---	22	---	nS
Q _{rr}	Reverse Recovery Charge ^(Note 1)		---	27	---	nC
t _{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L _S +L _D)				

Notes 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

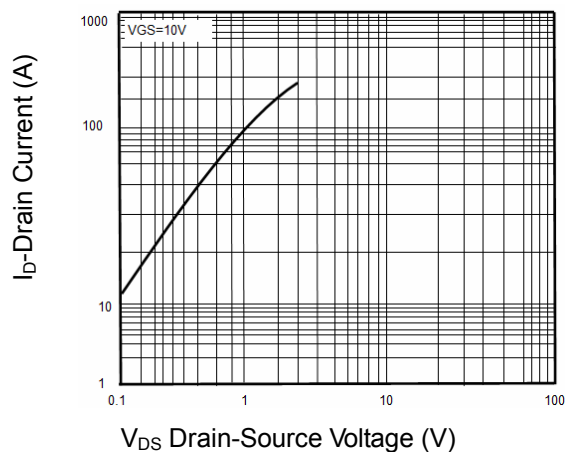


Figure2. Transfer Characteristics

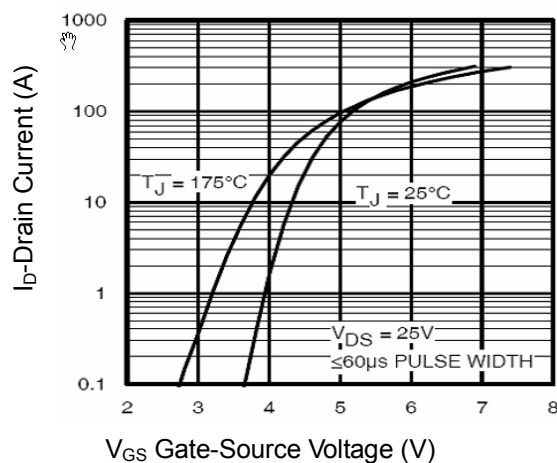


Figure3. BVDSS vs Junction Temperature

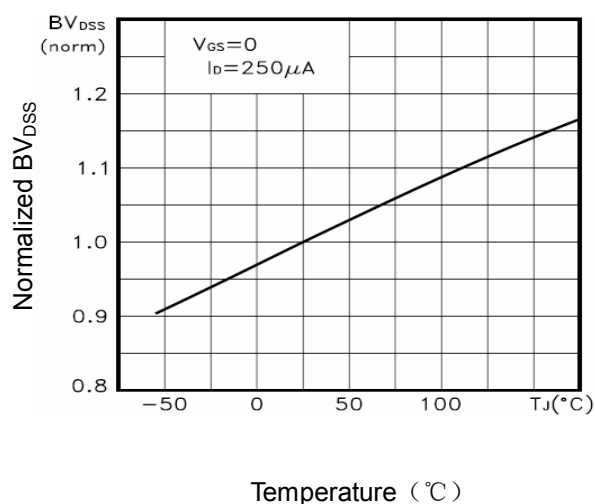


Figure4. ID vs Junction Temperature

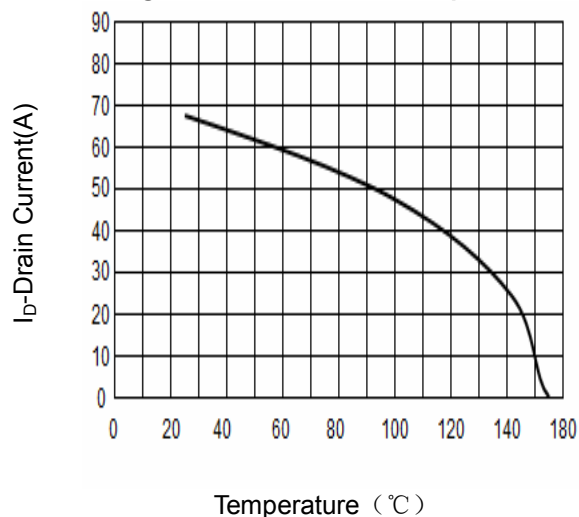


Figure5. VGS(th) vs Junction Temperature

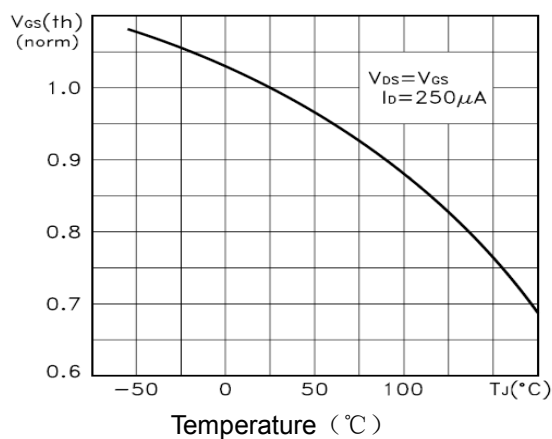


Figure6. Rdson Vs Junction Temperature

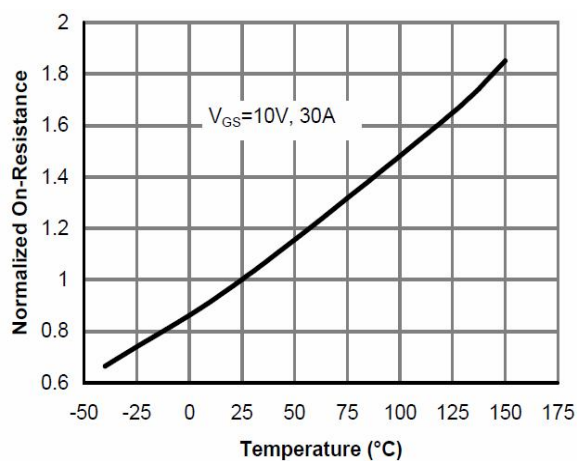
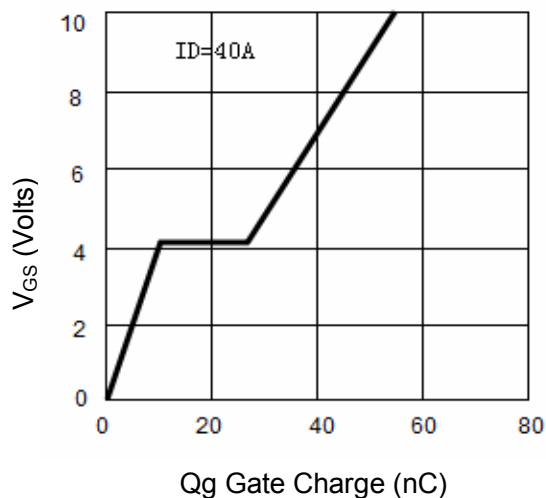
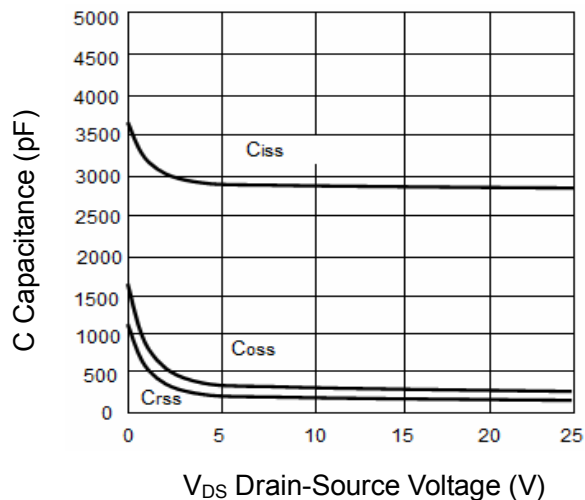
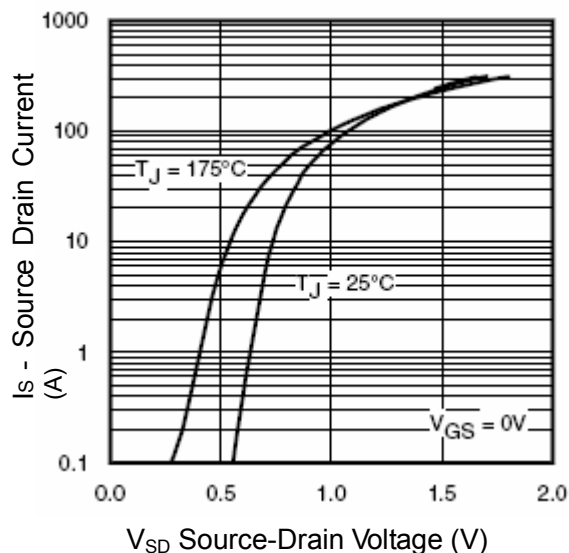
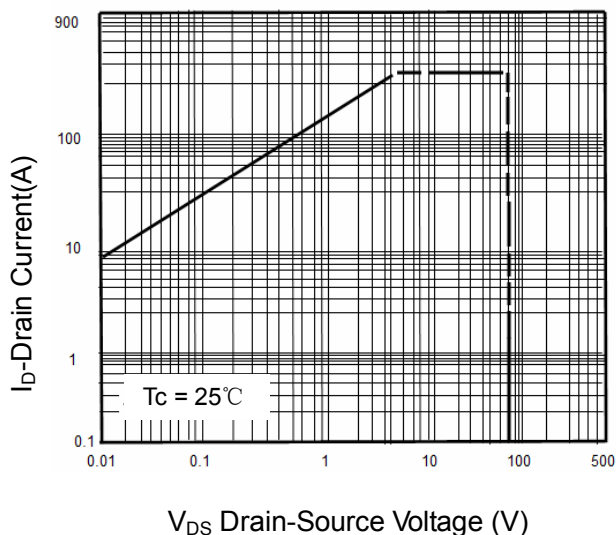
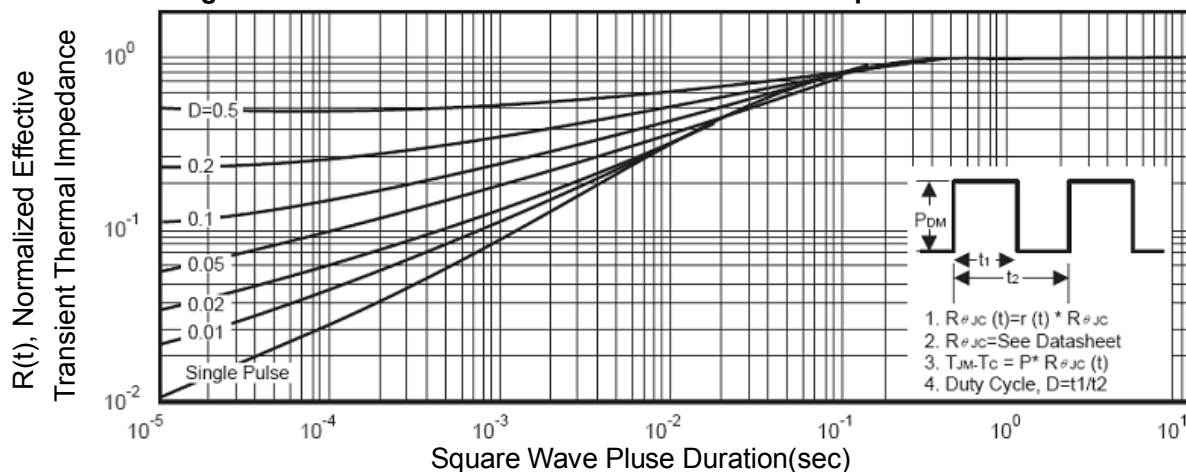
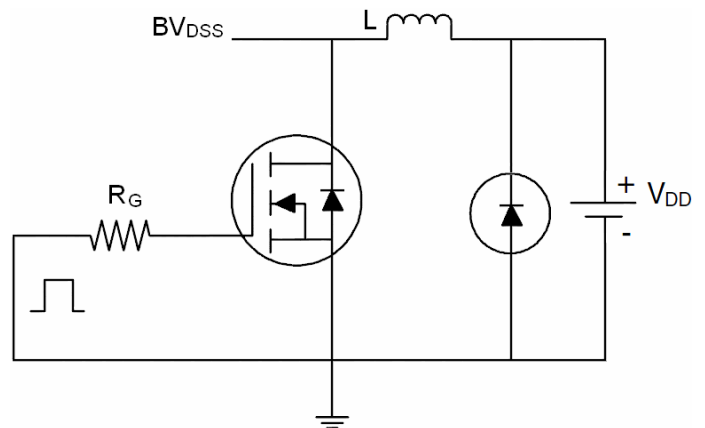
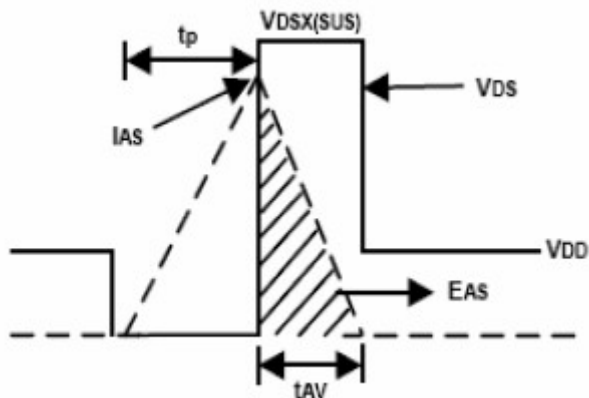


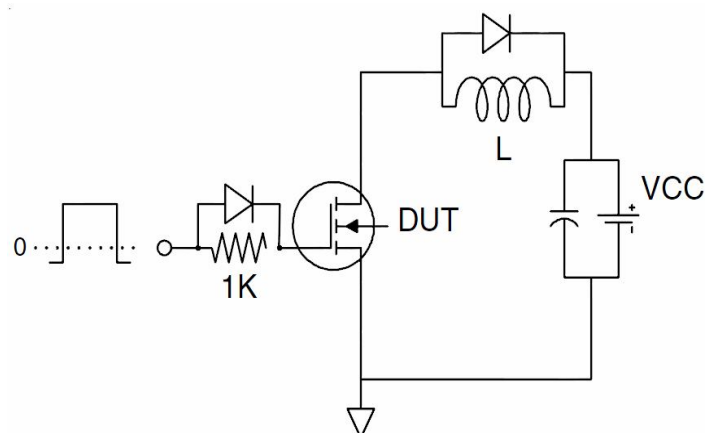
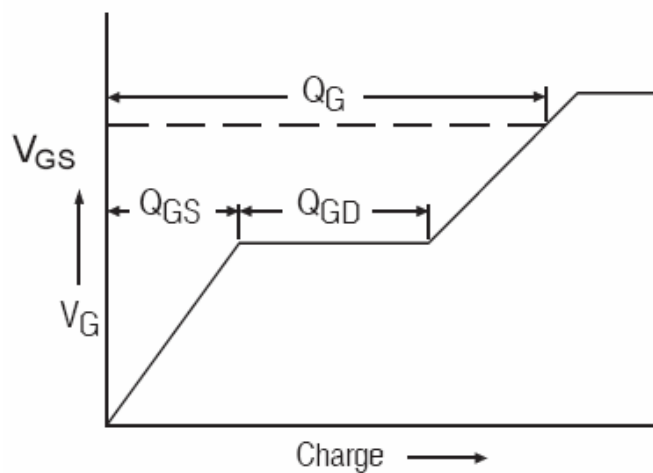
Figure7. Gate Charge

Figure8. Capacitance vs V_{DS}

Figure9. Source- Drain Diode Forward

Figure10. Safe Operation Area

Figure11. Normalized Maximum Transient Thermal Impedance


Test Circuit

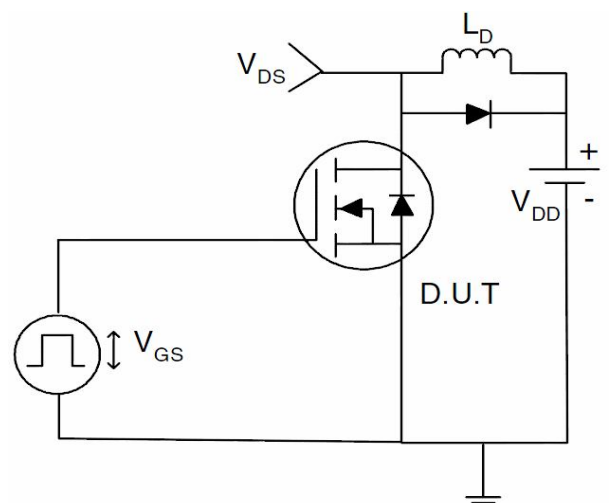
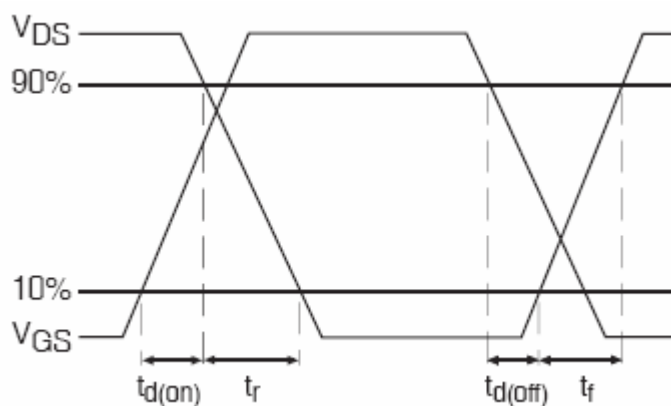
1) E_{AS} Test Circuits



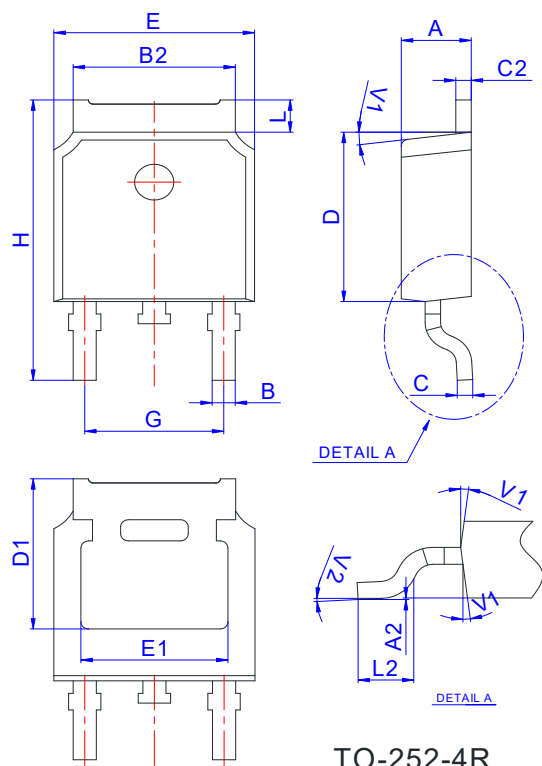
2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



Package Mechanical Data-TO-252-4R



TO-252-4R

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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